

N-Channel MOSFET Transistor

FEATURES

- · Drain Current -I_D= 3A@ T_C=25℃
- · Drain Source Voltage -V_{DSS}= 1200V(Min)
- · Static Drain-Source On-Resistance
- $-R_{DS(on)} = 4.5\Omega(Max)@V_{GS} = 10V$

APPLICATIONS

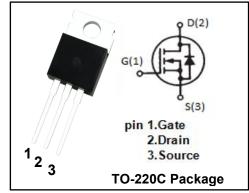
Switching

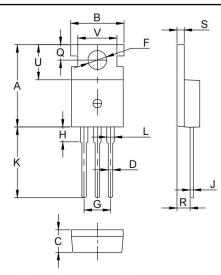
Absolute Maximum Ratings(T_C=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	1200	V	
V _{GS}	Gate-Source Voltage	±20	V	
I _D	Drain Current-Continuous	3.0	A	
Іпм	Drain Current-Single Pulsed	12	Α	
P_D	Total Dissipation @Tc=25℃	200	W	
Тј	Max. Operating Junction Temperature	150	°C	
T _{stg}	Storage Temperature	-55~150	$^{\circ}$	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th(J-c)}	Thermal Resistance Junction-to-Case	0.62	°C/W





DIM	mm		
	MIN	TYP.	MAX
Α	15.50	15.70	15.90
В	9.80	10.00	10.20
С	4.20	4.35	4.50
D	0.70	0.80	0.90
F	3.40	3.55	3.70
G	4.98	5.08	5.18
H	2.68	2.79	2.90
J	0.44	0.52	0.60
K	12.80	13.10	13.40
L	1.20	1.32	1.45
Q	2.70	2.80	2.90
R	2.30	2.50	2.70
S	1.29	1.32	1.35
U	6.45	6.55	6.65
V	8.66	8.76	8.86

ISF1219 eq IXTP3N120

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ELECTRICAL CHARACTERISTICS (Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID = 1.0mA	1200	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID = 0.25mA	2.5	-	5.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D = 1.5A	-	-	4.5	Ω
lgss	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} =0V	-	-	±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 1200V; V _{GS} = 0V	-	-	25	μА
V _{SD}	Diode forward voltage	I _{SD} = 3A; V _{GS} = 0V	-	-	1.5	V

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